

150V N-Channel Enhancement Mode MOSFET

Description

The AP10N15D es advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 150V$ $I_D = 10A$

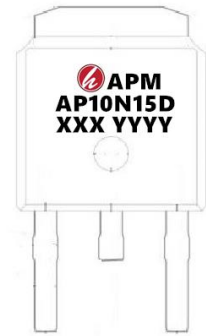
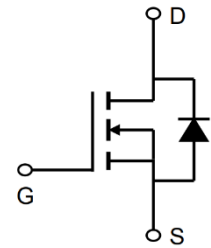
$R_{DS(ON)} < 280m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP10N15D	TO-252-3L	AP10N15D	2500

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	10	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	28	A
Maximum Power Dissipation	P_D	30	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ\text{C}$
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	5	$^\circ\text{C/W}$



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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	150	165	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.8	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A	-	175	280	mΩ
Gate resistance	R _G		-	1.7	-	Ω
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =7A	-	3	-	S
Input Capacitance	C _{ISS}	V _{DS} =75V, V _{GS} =0V, F=1.0MHz	-	550	-	PF
Output Capacitance	C _{OSS}		-	56	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	35	-	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =75V, R _L =10Ω V _{GS} =10V, R _G =6Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	20	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Q _g	V _{DS} =75V, I _D =7A, V _{GS} =10V	-	17.6	-	nC
Gate-Source Charge	Q _{gs}		-	2.7	-	nC
Gate-Drain Charge	Q _{gd}		-	4.5	-	nC
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =7A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to product

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Typical Characteristics

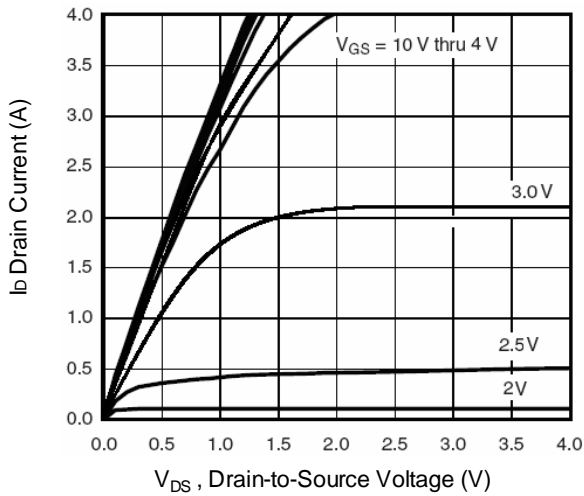


Fig.1 Typical Output Characteristics

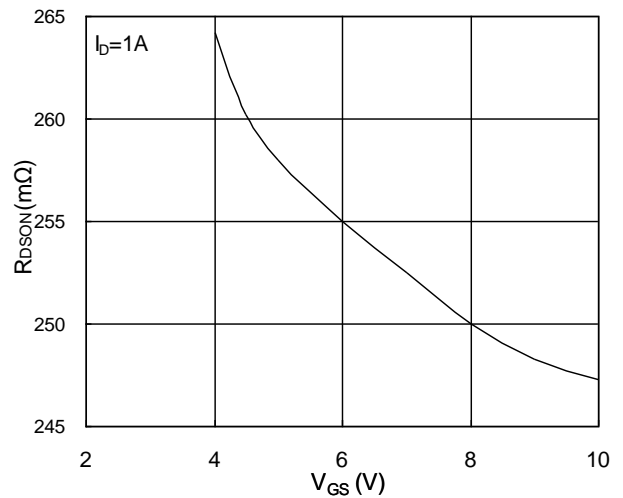


Fig.2 On-Resistance vs. Gate-Source

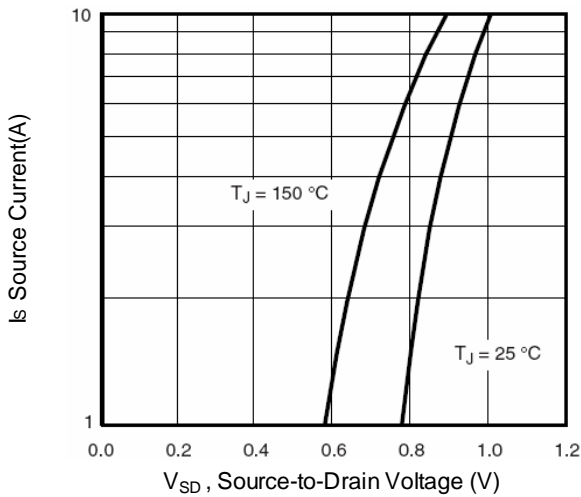


Fig.3 Forward Characteristics of Reverse

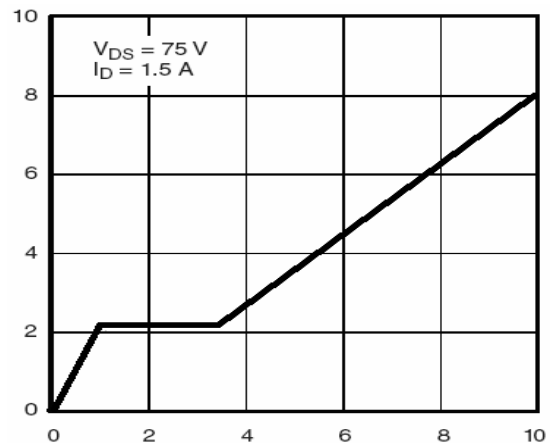


Fig.4 Gate-Charge Characteristics

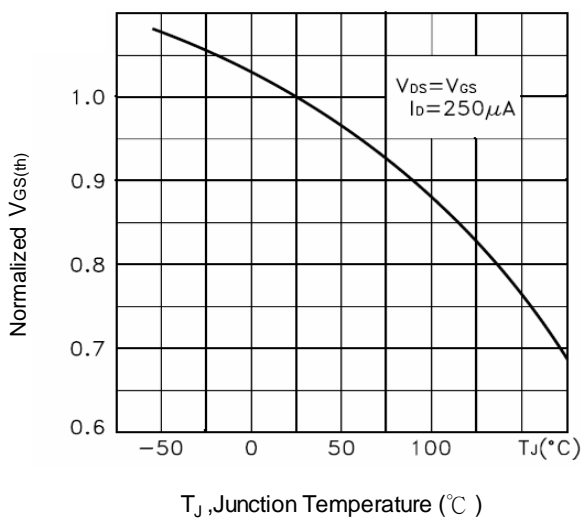


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

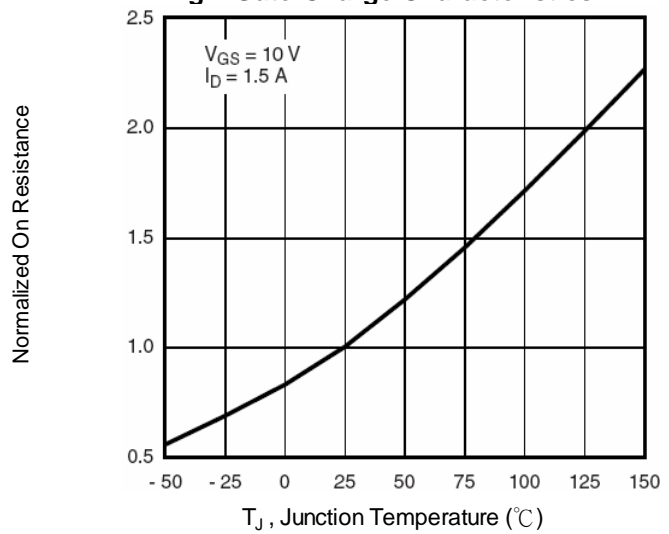


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



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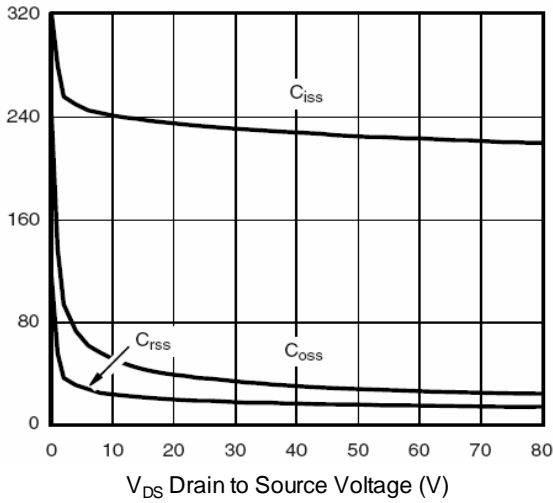


Fig.7 Capacitance

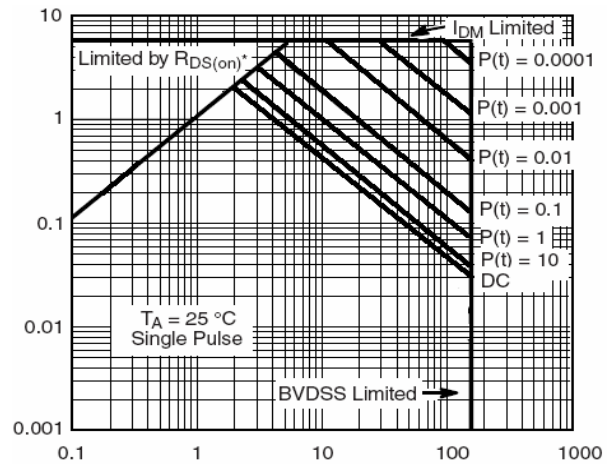


Fig.8 Safe Operating Area

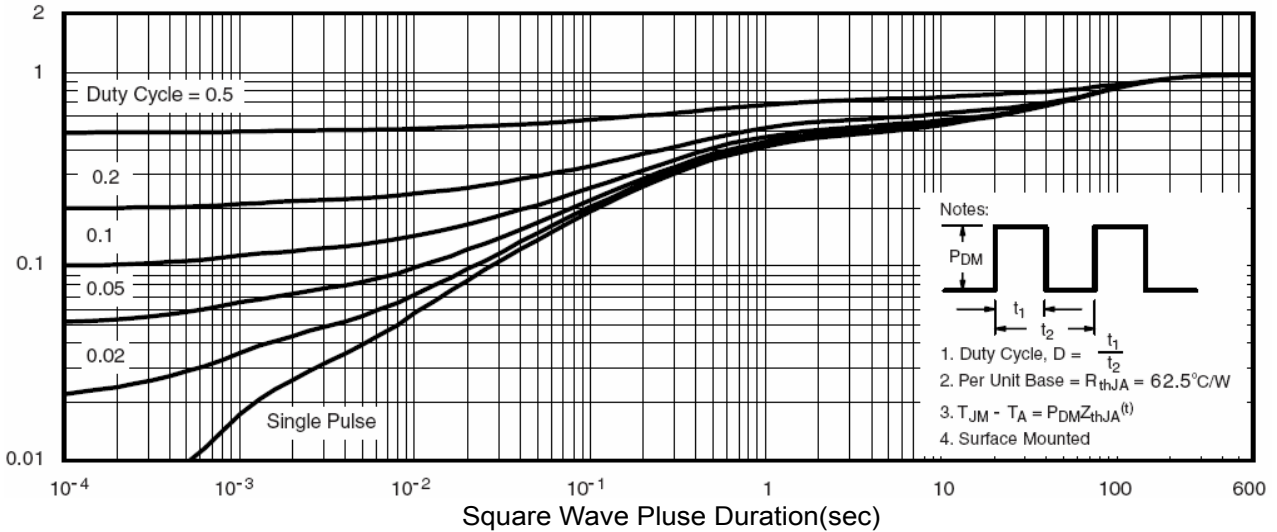


Fig.9 Normalized Maximum Transient Thermal Impedance

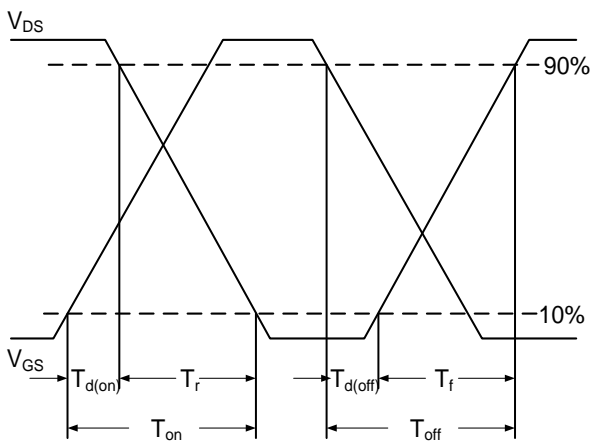


Fig.10 Switching Time Waveform

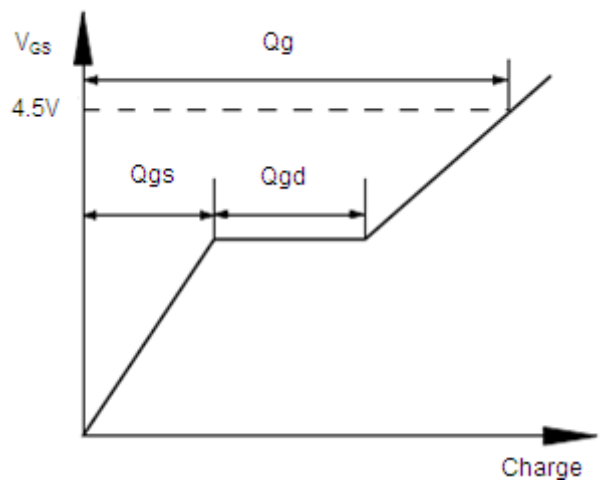
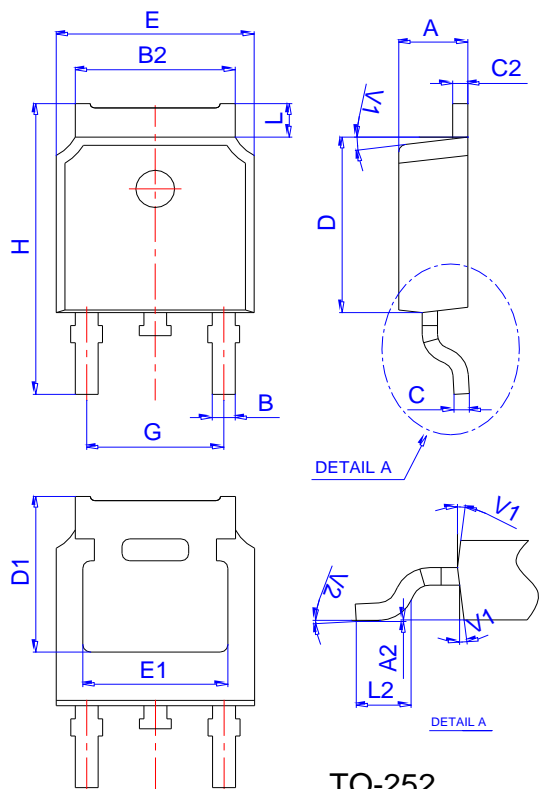


Fig.11 Gate Charge Waveform

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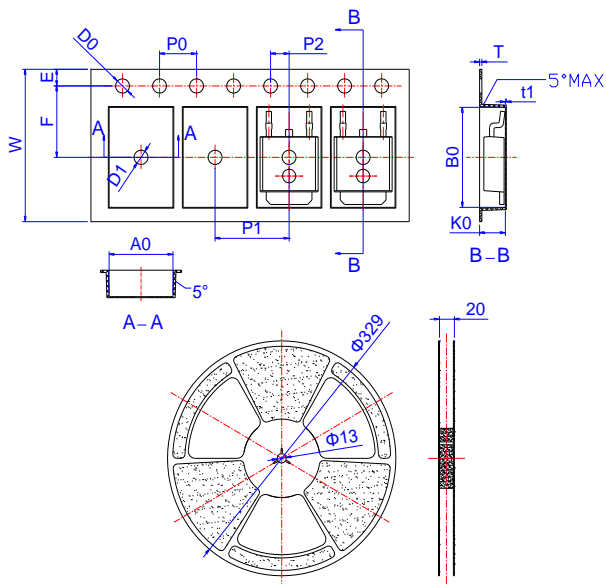
Package Mechanical Data



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°	7°	6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

150V N-Channel Enhancement Mode MOSFET**Attention**

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